



# Computational design of new multifunctional materials

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## Collaborators:

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ABINIT workshop, Paris 2004

## \$\$\$s:

NSF DMR, MRSEC and IGERT, DOE, ONR, ACS PRF.



# Plan for designing for multifunctionality



- ◆ Understand origin of each function separately (DFT)
- ◆ Design a trial compound with required properties (intuition/experience)
- ◆ Check that the trial compound indeed behaves as required (DFT)
- ◆ Persuade an experimentalist to make and characterize it!

*Computational design of multifunctional materials,*  
N.A. Spaldin and W.E. Pickett, JSSC, 176, 615 (2003)



# Interesting multifunctional materials:



- ◆ Magnetolectric multiferroics
  - ◆ Magnetic insulators (beyond LDA)
  - ◆ Visualization of lone pairs
  - ◆ Polarization, dielectric response
  - ◆ Spin-orbit coupling and non-collinearity
- ◆ Diluted magnetic semiconductors
  - ◆ Defects and impurities (large supercells)
  - ◆ Band gaps important (beyond LDA)
  - ◆ Grain boundary effects (large supercells)



# My group and their codes....

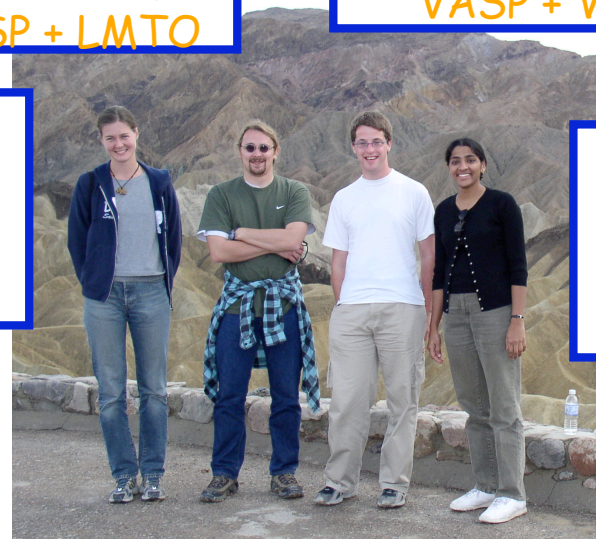


Stefano Sanvito (TCD)  
DMSs; **SIESTA**



Claude Ederer,  
ME coupling;  
**VASP + LMTO**

Rebecca  
Janisch, grain  
boundaries;  
**ABINIT**



Pio Battig, FM FEs;  
**VASP + Wien**

Priya Gopal,  
magnetic PEs;  
**ABINIT, VASP  
+ Pseudo-SIC**

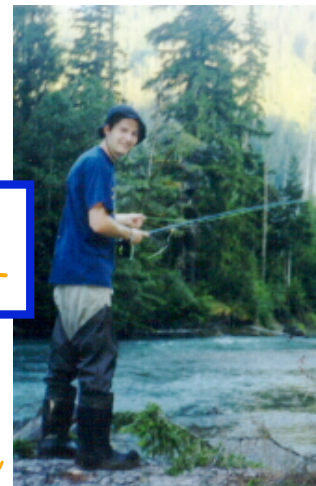
Alessio Filippetti (U.  
Cagliari), FMFEs;  
**PSEUDO-SIC**



Kim Goto, FM metal/  
Nanotubes; **SIESTA**

Chuck Schelle, Pb-free  
Piezoelectrics; **ABINIT**

**ABINIT** workshop,







# Is there a better way?



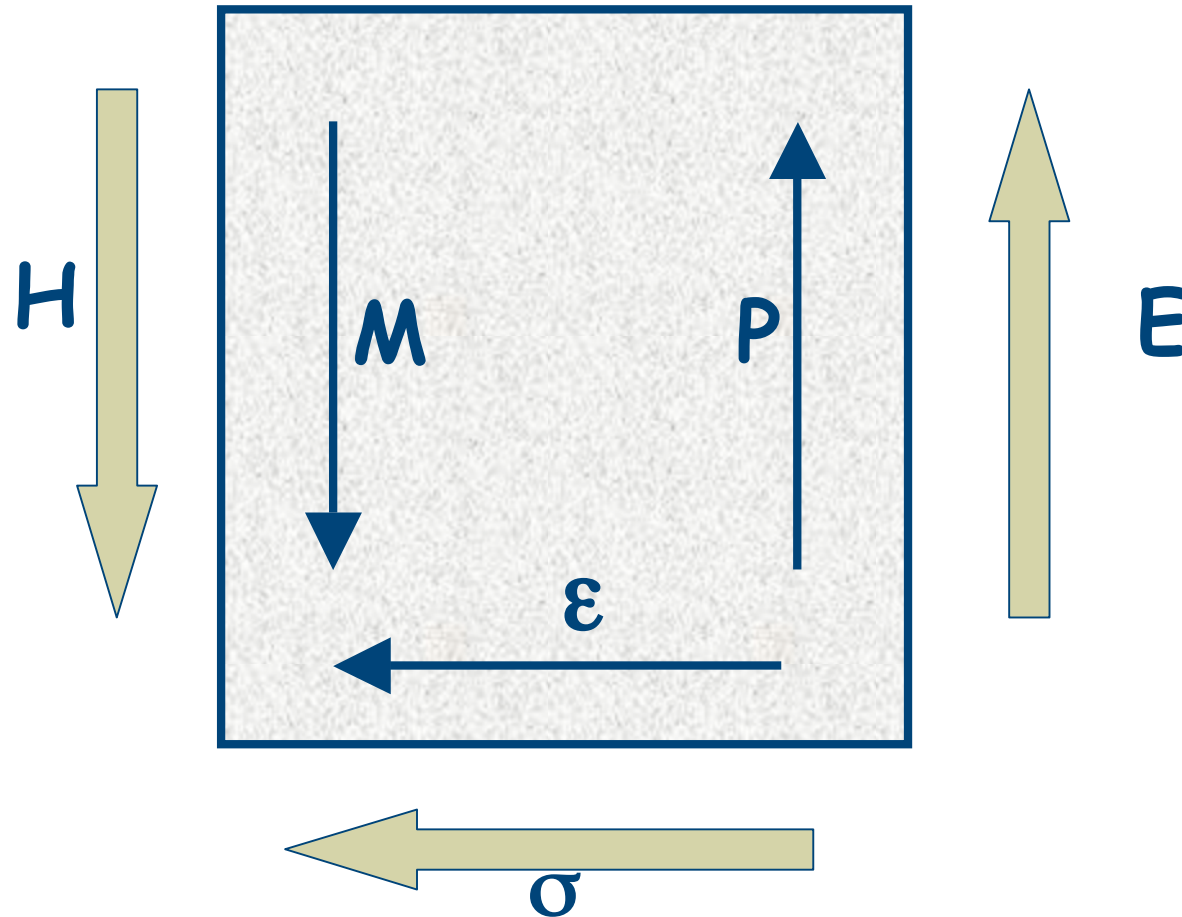
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Can we use just ONE code for a specific material design project?

Let's look at an example.....



# Multiferroic magnetoelectrics



Review: N.A. Hill, *Ann. Rev. Mat. Res.* **32**, 1-37 (2002).

ABINIT workshop, Paris 2004

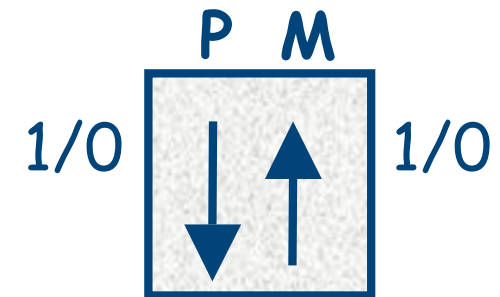


# Possible multiferroic applications?



## Device applications (long range):

- Multiple state memory elements
- Write to  $E$  / read from  $M$
- High  $\mu$ , high  $\varepsilon$  materials
- $E$  tunable magnetic properties (and vice versa)



## Recent observations:

- Giant field-tunable non-linear optical response
- Large magnetocapacitance

## Fundamental physics:



# Problem:



Almost none exist.

1<sup>st</sup> question: *Why are there so few magnetic ferroelectrics?*

N.A. Hill, *J. Phys. Chem. B* 104, 6694-6709 (2000)





# Requirements for magnetoelectric multiferroicity

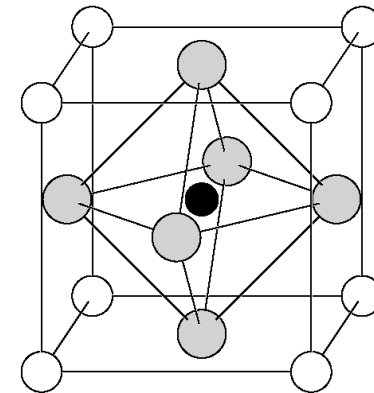


## ◆ Symmetry

1, 2, 2', m, m', 3, 3m', 4, 4m'm', m'm2', m'm'2', 6, 6m'm'

## ◆ Electrical Properties

## ◆ Chemistry - "d<sup>0</sup>-ness"



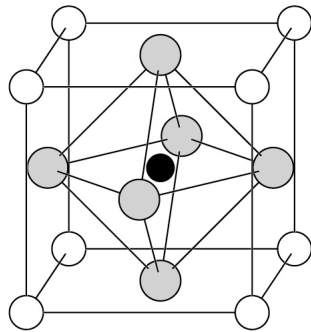
ION	Ti <sup>4+</sup> d <sup>0</sup>	Nb <sup>5+</sup> d <sup>0</sup>	Zr <sup>4+</sup> d <sup>0</sup>	Mn <sup>3+</sup> d <sup>4</sup>	Ti <sup>3+</sup> d <sup>1</sup>	V <sup>4+</sup> d <sup>1</sup>
SIZE (pm)	74.5	78.0	86.0	78.5	81.0	72.0



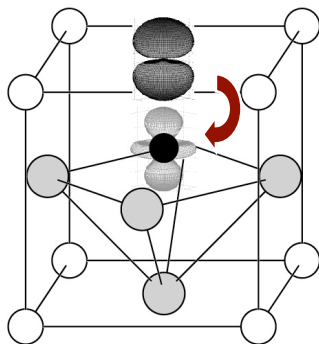
# Conventional mechanism for ferroelectricity:



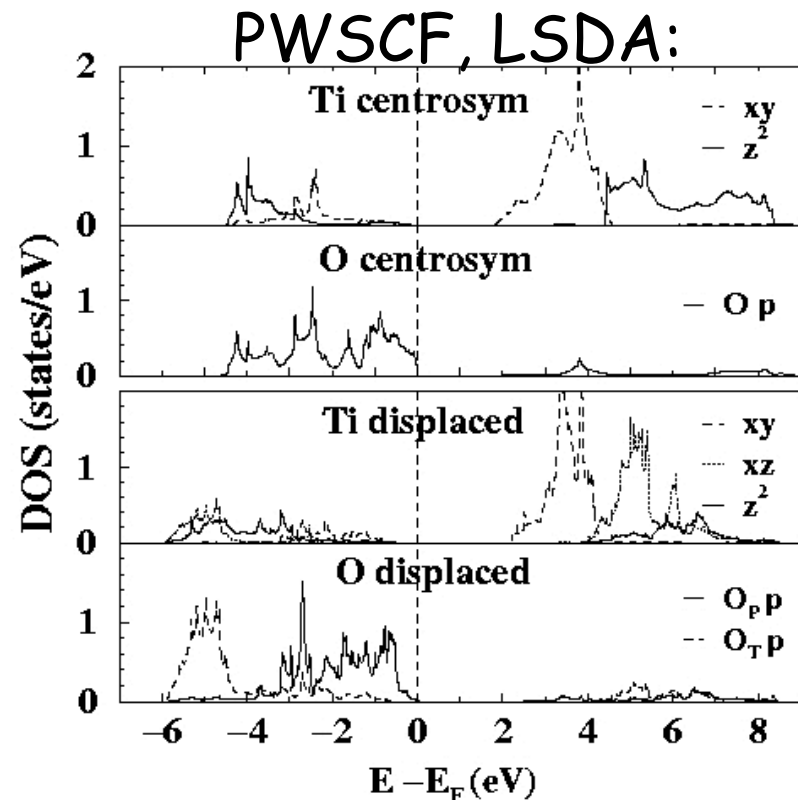
Ligand field stabilization of *empty* cation d orbitals by oxygen p electrons:



paraelectric



ferroelectric





# BUT magnetism requires localized electrons!

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In perovskite structure oxides the source of magnetic, localized electrons is usually the transition metal  $d$  electrons, e.g.  $\text{LaMnO}_3$ ,  $\text{SrRuO}_3$ , etc.

**BAD NEWS!**

Ferromagnetism requires  $d$  electrons

Ferroelectricity requires " $d^0$ -ness"

**CHEMICALLY INCOMPATIBLE!**



But.....

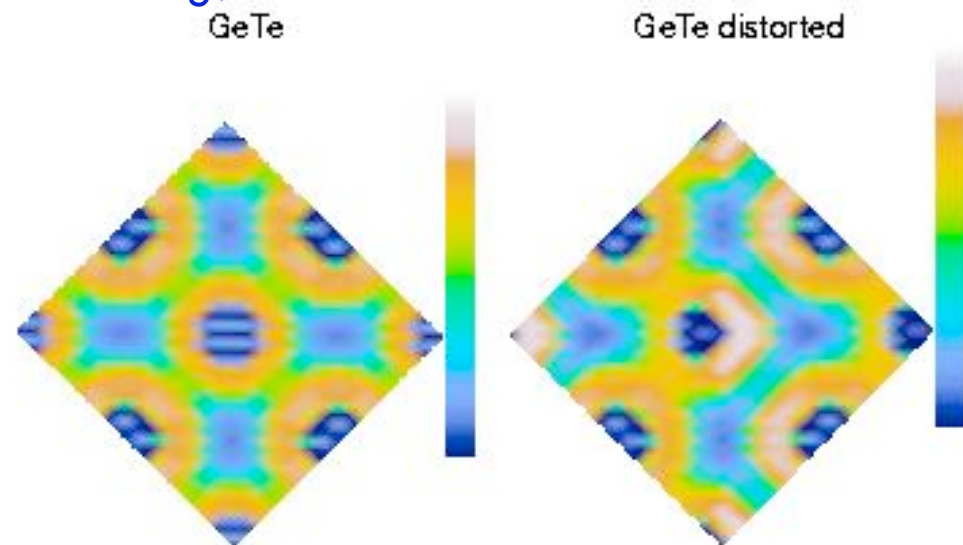


Alternative mechanism for ferroelectricity:

**Cation lone pair localization**

e.g. IV-VI compounds,  $\text{PbTiO}_3$ , etc.

U.V. Waghmare, N.A. Spaldin,  
H.C. Kandpal and R. Seshadri,  
*First principles indicators of  
metallicity and cation off-  
centricity in the IV-VI rock-  
salt chalcogenides of divalent  
Ge, Sn and Pb*, PRB **67**, 125111  
(2003).



(Stuttgart LMTO code)

**needs an  $(ns)^2$  pair of electrons**





# Perovskite design:



- ◆ Transition metal cation with  $d$  electrons for magnetism
- ◆ Ferro- (or ferri-) magnetic ordering of the above
- ◆ Large cation with  $(ns)^2$  electron configuration

$(6s)^2$ : Tl<sup>+</sup>, Pb<sup>2+</sup>, Bi<sup>3+</sup>

$(5s)^2$ : In<sup>+</sup>, Sn<sup>2+</sup>, Sb<sup>3+</sup>

$(4s)^2$ : Ga<sup>+</sup>, Ge<sup>2+</sup>, As<sup>3+</sup>



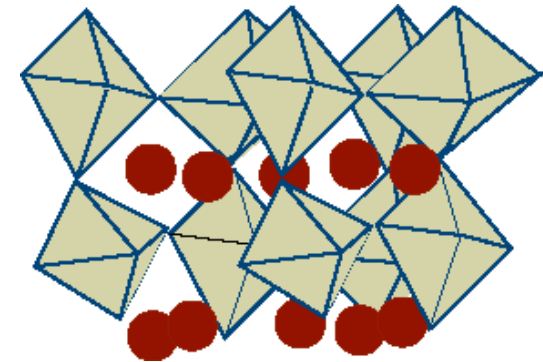
# Candidate multiferroic: $\text{BiMnO}_3$ ?



## What was known:

- ◆ Distorted cubic perovskite structure
- ◆ Ferromagnetic! ( $T_c = 100\text{K}$ )

Structure Determination:  
Monoclinic,  $C2$   
T.Atou et al., J. Sol. State. Chem.  
**145, 639 (1999).**



## Use DFT to check:

- ◆ Ferroelectric (and why)?
- ◆ *Intrinsically ferromagnetic?*



# What kind of DFT should we use?



**LSDA?** Usually OK for ferroelectrics, but not for **MAGNETIC** ferroelectrics! Tiny gap for the distorted structure; metal for the high symmetry phase.

Beyond-LDA methods, **LDA+U** or Self-interaction-corrected (**SIC**), are needed to calculate the polarization



# Self-Interaction



The self-interaction is the interaction of an electron's charge with the Coulomb and exchange-correlation potential generated by the same electron.

Consequences:

**Underestimated:**

- binding energies
- on-site Coulomb energies (Hubbard  $U$ )
- exchange splittings of d and f states

**Overestimated:**

- anion p - cation d hybridizations
- corresponding band widths ( $W$ )

Suppression of  $U$  and overestimation of  $W$  is a problem for materials with partially filled d states

where, in real life,  $U \gg W$

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# Solution: pseudo-SIC method - subtract off the exchange and correlation self-interaction within a pseudopotential formalism

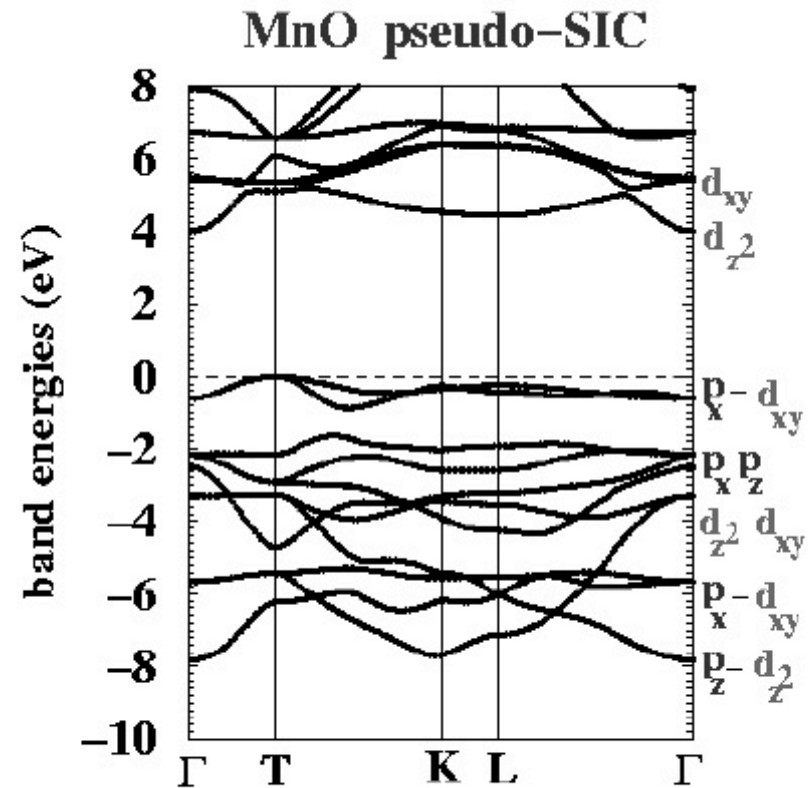
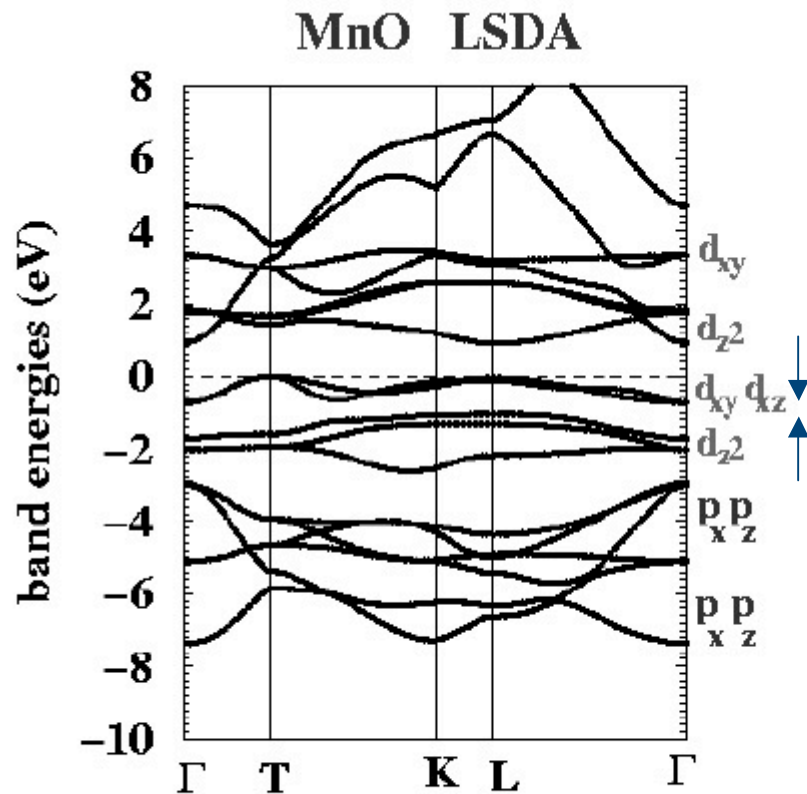


A. Filippetti and N.A. Spaldin, *Self-interaction corrected pseudopotential scheme for magnetic and strongly correlated systems*, Phys. Rev. B **67**, 125109 (2003).

## Builds on:

- ◆ Perdew and Zunger, PRB **23**, 5048 (1981). Extensive discussion and successful application to atoms and molecules.
- ◆ Svane et al., 1994 – present. Application of fully self-consistent SIC to solids. (impressive but expensive! LMTO implementation).
- ◆ Vogel et al., 1996-98. SIC pseudopotentials used in regular LDA calculation. Successful and cheap

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- gap too small and wrong character (Mott-Hubbard)
- incorrect d-p splitting
- magnetic moment too small

- } strong d-p mixing
- } no d-p splitting
- } large gap
- } intermediate charge-transfer/  
Mott Hubbard regime
- } correct magnetic moment

**NOTE: pseudo-SIC results are very similar to LDA+U!**



# Is $\text{BiMnO}_3$ ferroelectric and intrinsically ferromagnetic?

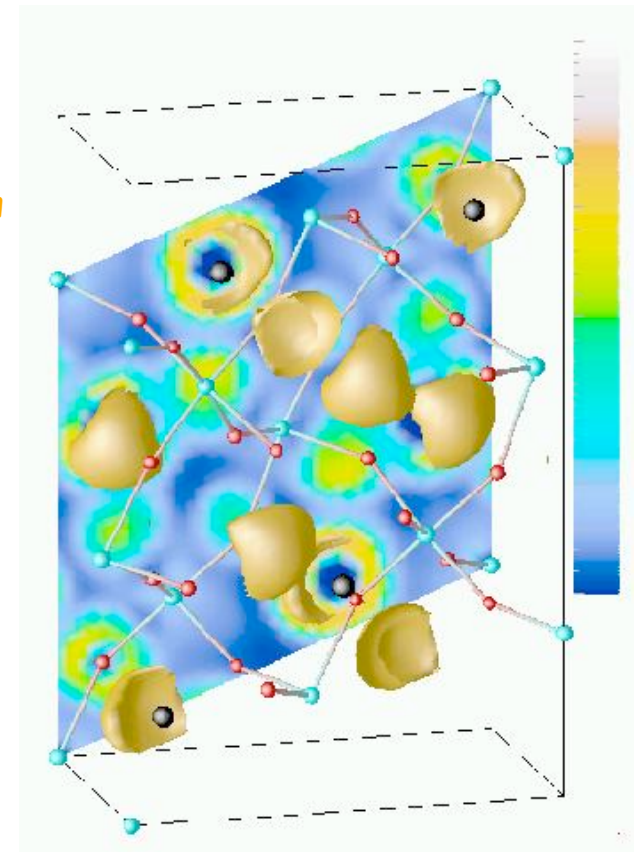


YES!

N.A. Hill and K.M. Rabe, *First-principles investigation of ferromagnetism and ferroelectricity in bismuth manganite*, *Phys. Rev. B* **59**, 8759 (1999).

DFT Calculations predict:

- ◆ Ferromagnetic ground state
- ◆ Strong ferroelectric instability in FM  $\text{BiMnO}_3$  (calculated polarization of  $\sim 70 \mu\text{C}/\text{cm}^2$ )
- ◆ Ferroelectricity results from - O displacement!



R. Seshadri and N.A. Hill, *Visualizing the role of Bi 6s "lone pairs" in the off-center distortion in ferromagnetic  $\text{BiMnO}_3$* , *Chemistry of Materials* **13**, 2892 (2001).



# Plan for designing for multifunctionality



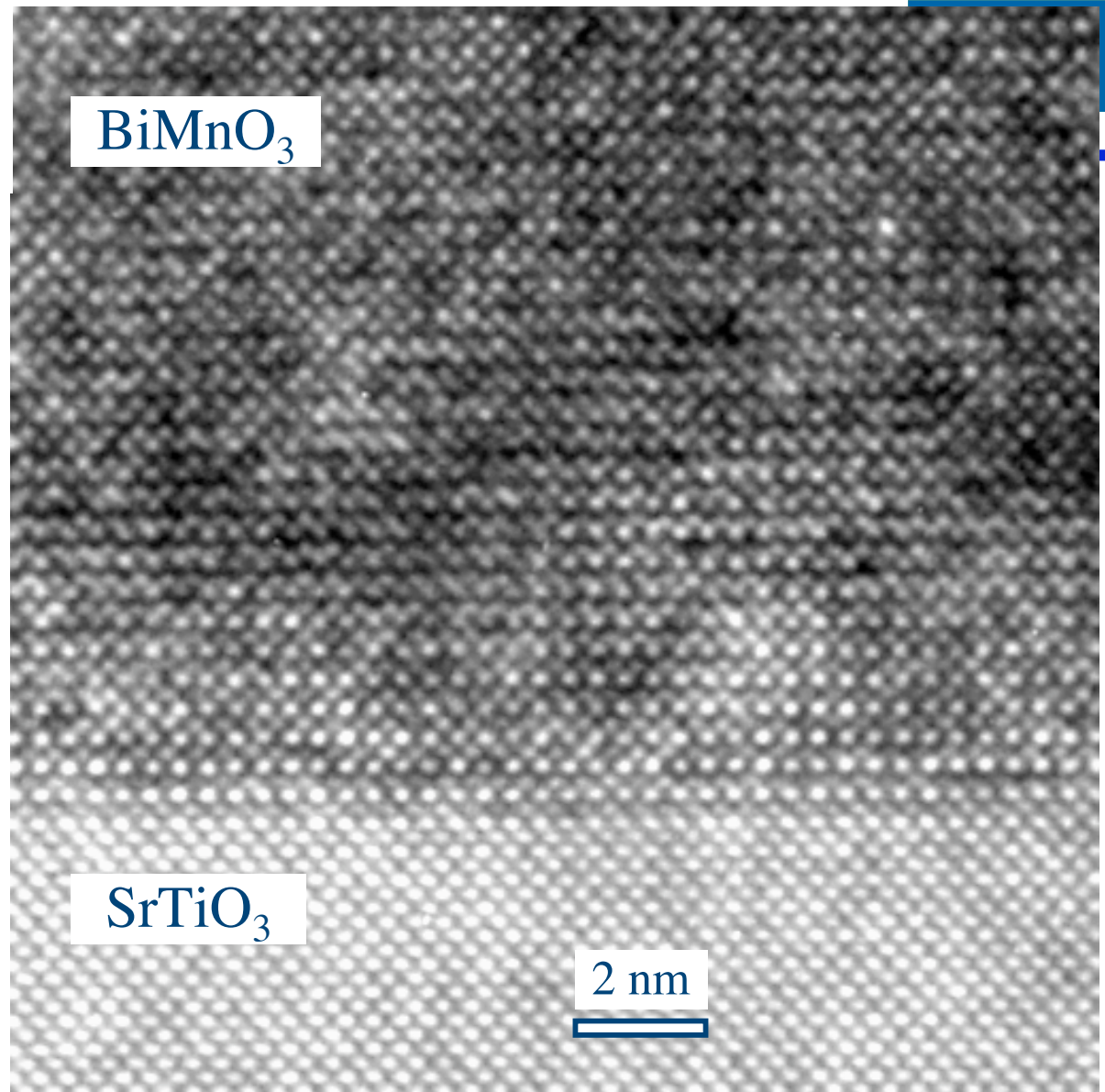
Understand origin of each function separately (DFT)

Design a trial compound with required properties (intuition/experience)

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- Persuade an experimentalist to make and

From Darrell Schlom:



Interface between SrTiO<sub>3</sub> and BiMnO<sub>3</sub>

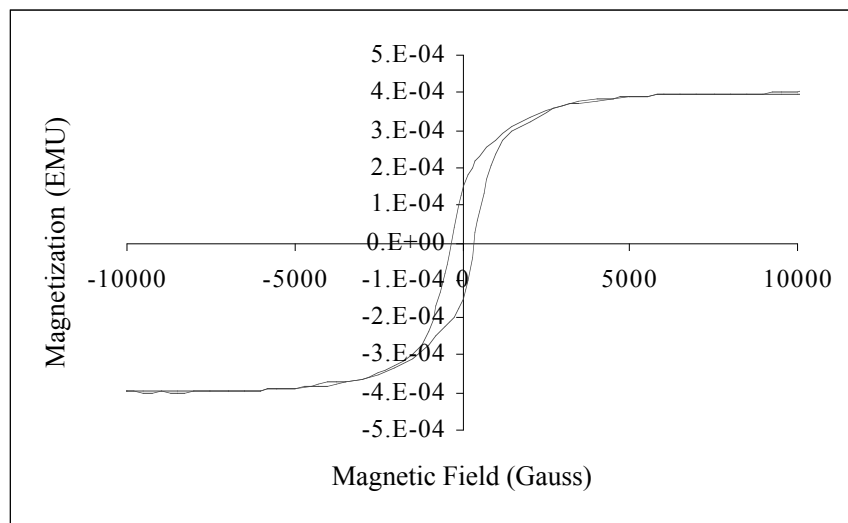
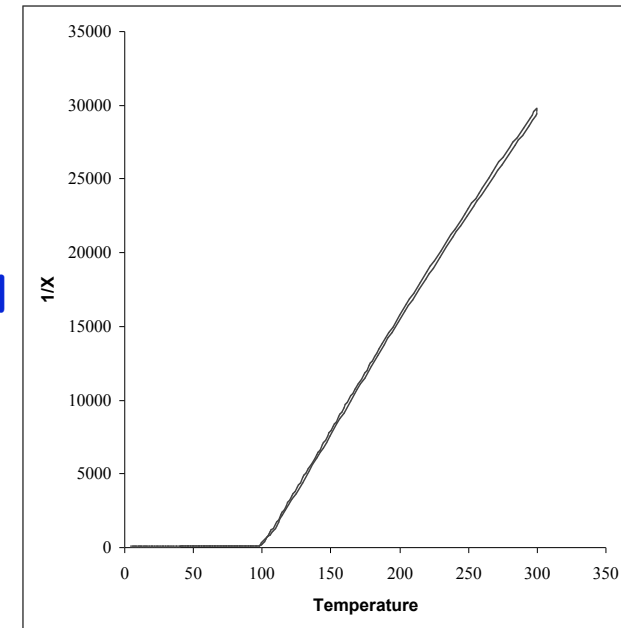
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# Magnetic properties



Magnetic characterization of the bulk  $\text{BiMnO}_3$  sample: inverse susceptibility vs. temperature, indicating a ferromagnetic material with  $T_c=105$  K.



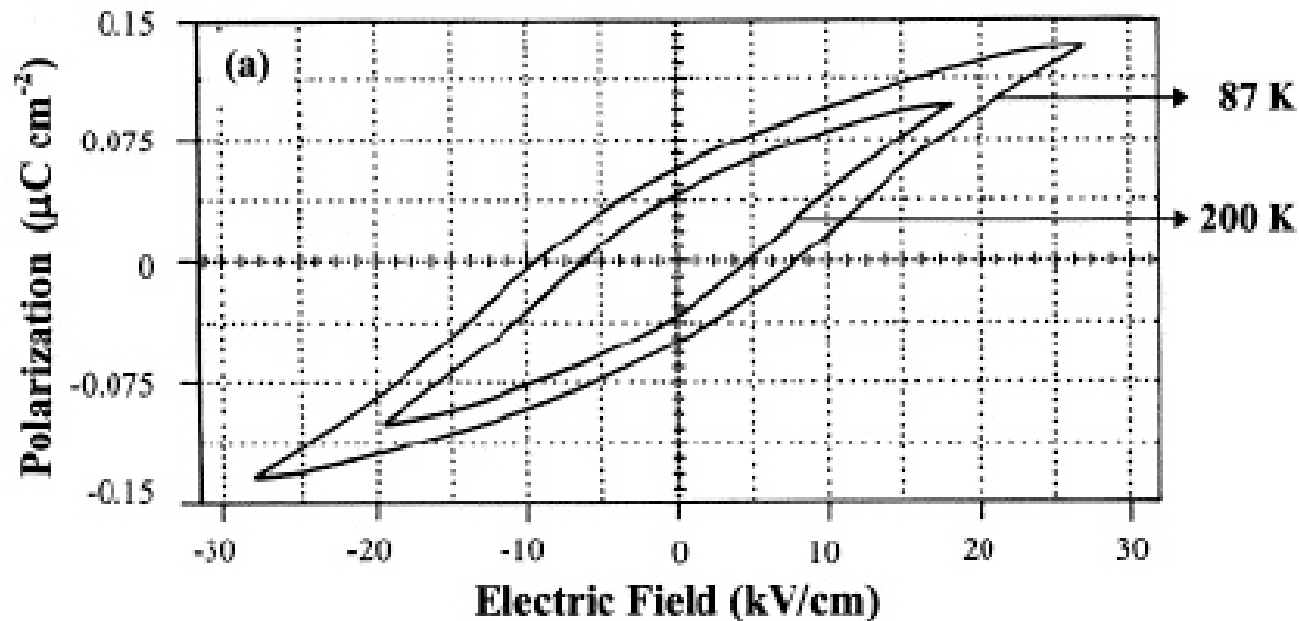
Magnetic hysteresis loop, measured at 10 K, of PLD grown  $\text{BiMnO}_3$  on  $\text{SrTiO}_3$ .

A.M. Santos, S. Parashar, A.R. Raju, Y.S. Zhao, A.K. Cheetham and C.N.R. Rao, *Evidence for the likely occurrence of magnetoferroelectricity in  $\text{BiMnO}_3$* , Sol. Stat. Comm. 122, 49 (2002).





# Experimental Data: Ferroelectric hysteresis in $\text{BiMnO}_3$



A.M. Santos, S. Parashar, A.R. Raju, Y.S. Zhao, A.K. Cheetham and C.N.R. Rao, *Evidence for the likely occurrence of magnetoferroelectricity in  $\text{BiMnO}_3$* , Sol. Stat. Comm. 122, **49** (2002).





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# Issues:



## Physics:

- ◆ Ferromagnetic Curie temperature of 100K (and why is it ferromagnetic anyway)
- ◆ Leaky! (Measured  $P$  lower than predicted; polarization lost just above room temperature)
- ◆ Need to understand origin of ferromagnetism, and to choose materials that are easier to grow

## Computational:

- ◆ Relationship between magnetization direction

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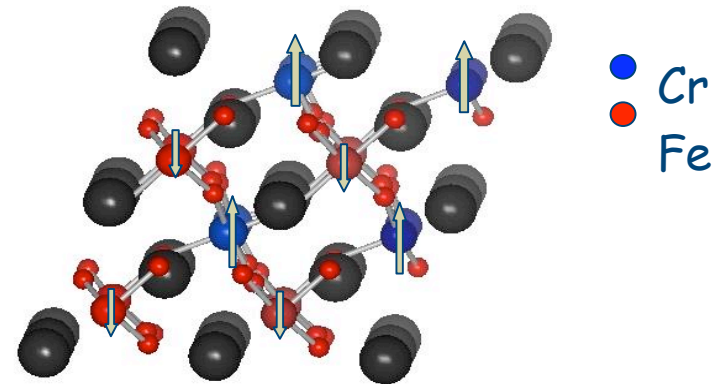
# Better choices for robust magnetic ferroelectrics:



## Ferrimagnets (more strongly insulating)

We predict (VASP, LDA+U) for (111) layered  $\text{Bi}_2\text{FeCrO}_6$

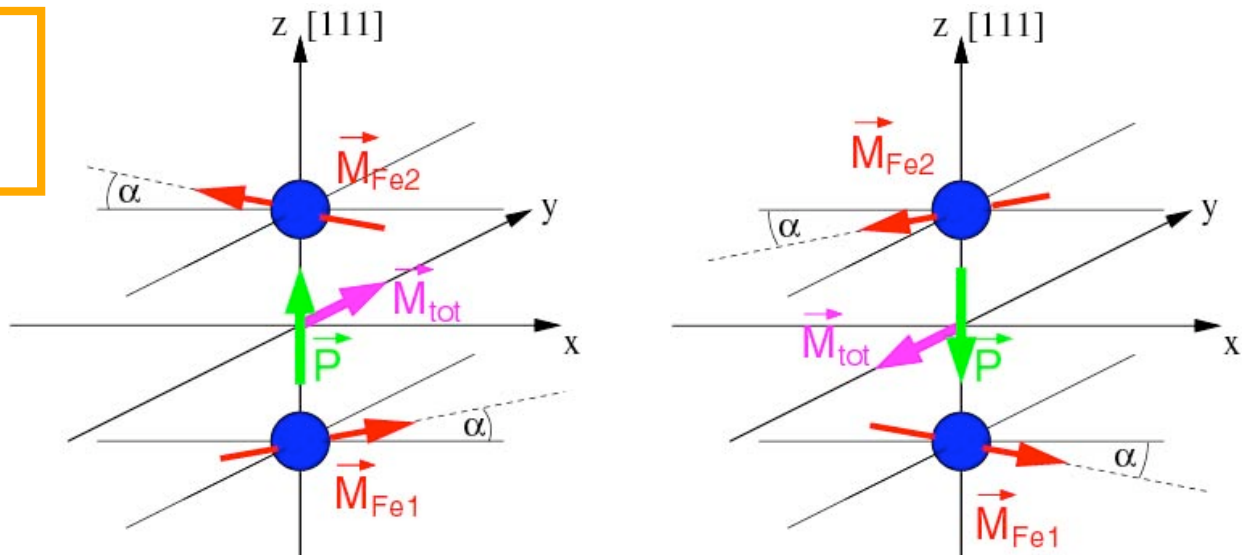
- Magnetic moment =  $2 \mu\text{B}/\text{unitcell}$
- Spontaneous polarization =  $70 \mu\text{C}/\text{cm}^2$



## Weak ferromagnets - coupled M and P!

e.g.  $\text{BiFeO}_3$

(LDA+U, SO coupling;  
VASP/LMTO)





# Conclusions/Discussion points



- ◆ DFT-based methods are invaluable in the design of new materials
- ◆ Complex, multifunctional materials require a range of techniques (different physics AND different algorithms)
- ◆ Can we (should we) try to incorporate them all into one code?

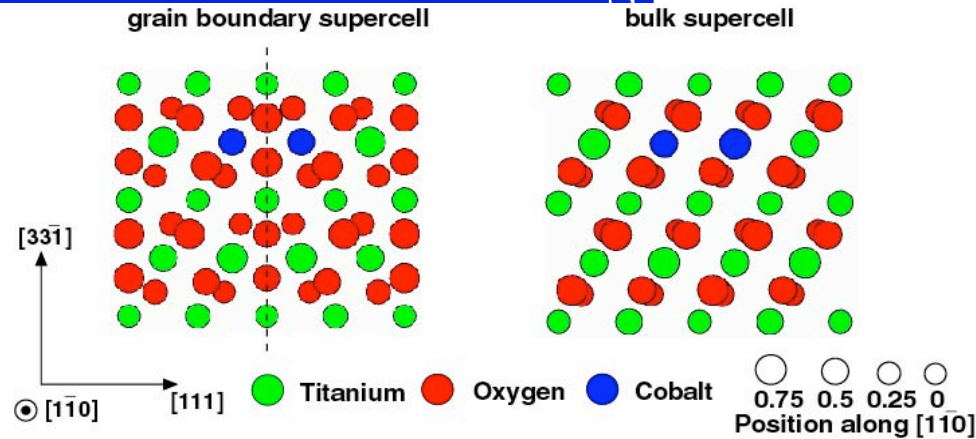


# Ongoing Work



## Grain boundary effects in $(\text{Co,Ti})\text{O}_2$ :

We identified a likely grain boundary in anatase  $\text{TiO}_2$ :  $\Sigma 5$   $(113)[110]$



Now we're calculating the influence on magnetic properties....

## Piezoelectric magnetic semiconductors, e.g. $(\text{Zn,Mn})\text{O}$ :

- MnO in wurtzite structure is strongly piezoelectric BUT
- $\times$   $(\text{Zn,TM})\text{O}$  needs carriers (preferably holes!) for ferromagnetism



Possible device architecture

$(\text{Zn,Co,Cu})\text{O}$
ZnO
$(\text{Zn,Co,Cu})\text{O}$
ZnO

P

